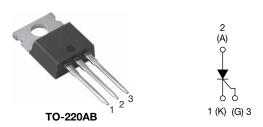
VS-10TTS08PbF, VS-10TTS08-M3

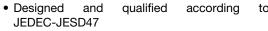
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Thyristor High Voltage, Phase Control SCR, 10 A



PRODUCT SUMMARY				
Package	TO-220AB			
Diode variation	Single SCR			
I _{T(AV)}	6.5 A			
V _{DRM} /V _{RRM}	800 V			
V _{TM}	1.15 V			
I _{GT}	15 mA			
T _J	- 40 °C to 125 °C			

FEATURES





• 125 °C max. operating junction temperature

Material categorization:
For definitions of compliance please see

ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

www.vishay.com/doc?99912

 Typical usage is in input rectification crowbar (soft star) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-10TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS				
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	13.5	17	А		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	TEST CONDITIONS VALUES			
I _{T(AV)}	Sinusoidal waveform	6.5	Α		
I _{T(RMS)}		10	A		
V _{RRM} /V _{DRM}		800	V		
I _{TSM}		110	А		
V _T	6.5 A, T _J = 25 °C	1.15	V		
dV/dt		150	V/µs		
dl/dt		100	A/µs		
T _J	Range	- 40 to 125	°C		

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA
VS-10TTS08PbF, VS-10TTS08-M3	800	800	1.0

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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 112 °C, 180° conduction half sine wave		6.5	
Maximum RMS on-state current	I _{T(RMS)}	1 _C = 112 G, 180 Conduc	Clion riali sirie wave	10	Α
Maximum peak, one-cycle,	1	10 ms sine pulse, rated V	_{RRM} applied, T _J = 125 °C	95	_ A
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no volta	age reapplied, T _J = 125 °C	110	
Maximum 12t for fucing	l ² t	10 ms sine pulse, rated V	RRM applied, T _J = 125 °C	45	A ² s
Maximum I ² t for fusing	1-1	10 ms sine pulse, no volta	age reapplied, T _J = 125 °C	64	A-S
Maximum I ² √t for fusing	I²√t	$t = 0.1$ ms to 10 ms, no voltage reapplied, $T_J = 125$ °C		640	A²√s
Maximum on-state voltage drop	V _{TM}	6.5 A, T _J = 25 °C		1.15	V
On-state slope resistance	r _t	T _{.I} = 125 °C		17.3	mΩ
Threshold voltage	V _{T(TO)}	1J=125 C		0.85	V
Maximum reverse and direct leakage	1 /1	T _J = 25 °C	V Detect V A/	0.05	
current	I _{RM} /I _{DM}	T _J = 125 °C	V_R = Rated V_{RRM}/V_{DRM}	1.0]
Typical holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		30	mA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		50	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max.}$, linear to 80 %, $V_{DRM} = R_q - k = Open$		150	V/µs
Maximum rate of rise of turned-on current	dl/dt			100	A/μs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0	VV
Maximum peak positive gate current	+l _{GM}		1.5	Α
Maximum peak negative gate voltage	-V _{GM}		10	V
	l _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	20	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	15	mA
		Anode supply = 6 V, resistive load, T _J = 125 °C	10	
Marrian was reliand DC and	V _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	1.2	
Maximum required DC gate voltage to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	1	\
voltage to trigger		Anode supply = 6 V, resistive load, T _J = 125 °C	0.7	V
Maximum DC gate voltage not to trigger	V_{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.2	
Maximum DC gate current not to trigger	I_{GD}	ij = 125 C, v _{DRM} = nated value	0.1	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8	
Typical reverse recovery time	t _{rr}	T _J = 125 °C	3	μs
Typical turn-off time	t _q	1J = 125 C	100	



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque ——	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf · in)
Marking device			Case style TO-220AB	10TT:	S08

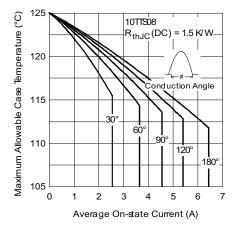


Fig. 1 - Current Rating Characteristics

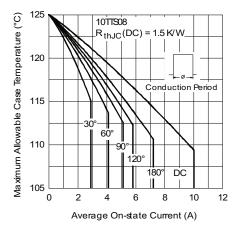


Fig. 2 - Current Rating Characteristic

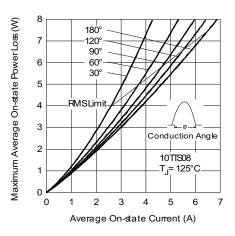


Fig. 3 - On-State Power Loss Characteristics

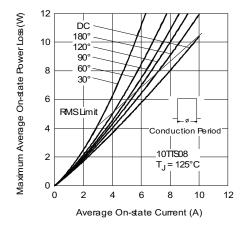


Fig. 4 - On-State Power Loss Characteristics

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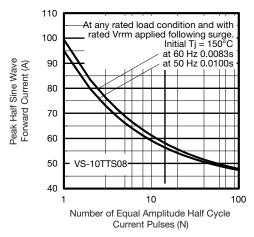


Fig. 5 - Maximum Non-Repetitive Surge Current

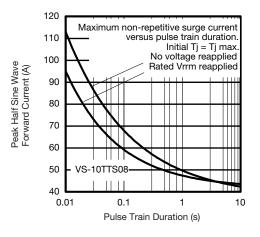


Fig. 6 - Maximum Non-Repetitive Surge Current

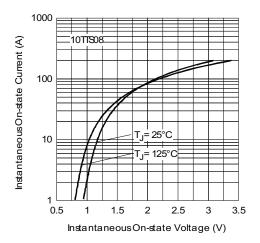


Fig. 7 - On-State Voltage Drop Characteristics

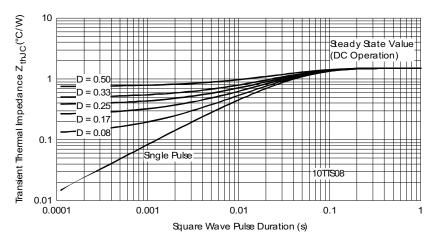


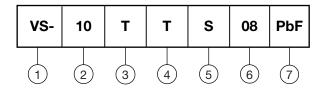
Fig. 8 - Thermal Impedance ZthJC Characteristics

VS-10TTS08PbF, VS-10TTS08-M3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = Converter grade

6 - Voltage code x 100 = V_{RRM}

7 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-10TTS08PbF	50	1000	Antistatic plastic tubes	
VS-10TTS08-M3	50	1000	Antistatic plastic tubes	

LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95222			
Part marking information	TO-220AB PbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028			



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